

IGBT

GD15PJY120F1S

1200V/15A PIM in one-package

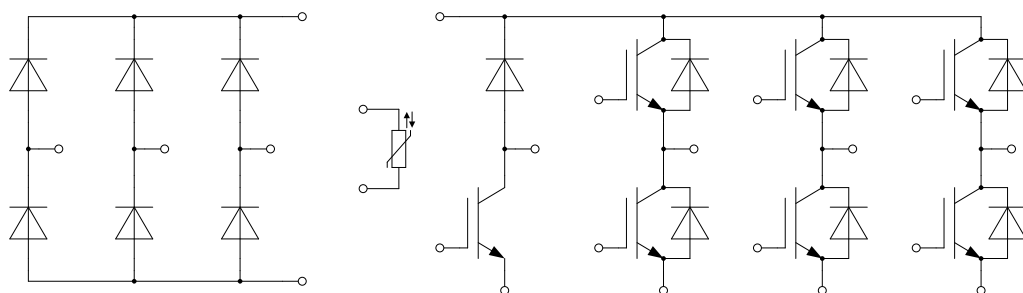
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT-inverter**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	30	A
	@ $T_C=100^{\circ}\text{C}$	15	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	30	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	118	W

Diode-inverter

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	15	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	30	A

Diode-rectifier

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
I_O	Average Output Current 50Hz/60Hz,sine wave	15	A
I_{FSM}	Surge Forward Current $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	270	A
I^2t	I^2t -value, $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	360	A^2s

IGBT-brake

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	20	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	92	W

Diode-brake

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	20	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature(inverter,brake)	175	$^{\circ}\text{C}$
	Maximum Junction Temperature (rectifier)	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V

IGBT-inverter Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=15\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.70	2.15	V
		$I_C=15\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		1.95		
		$I_C=15\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.38\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.2	6.0	6.8	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		1.55		nF
C_{res}	Reverse Transfer Capacitance			0.04		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.12		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		59		ns
t_r	Rise Time			63		ns
$t_{d(off)}$	Turn-Off Delay Time			201		ns
t_f	Fall Time			149		ns
E_{on}	Turn-On Switching Loss			1.39		mJ
E_{off}	Turn-Off Switching Loss			0.85		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		59		ns
t_r	Rise Time			70		ns
$t_{d(off)}$	Turn-Off Delay Time			283		ns
t_f	Fall Time			196		ns
E_{on}	Turn-On Switching Loss			1.87		mJ
E_{off}	Turn-Off Switching Loss			1.24		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		59		ns
t_r	Rise Time			70		ns
$t_{d(off)}$	Turn-Off Delay Time			288		ns
t_f	Fall Time			221		ns
E_{on}	Turn-On Switching Loss			2.09		mJ
E_{off}	Turn-Off Switching Loss			1.39		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		60		A

Diode-inverter Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=15\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		2.05	2.50	V
		$I_F=15\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		2.00		
		$I_F=15\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		2.00		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=15\text{A},$ $-di/dt=550\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		1.1		μC
I_{RM}	Peak Reverse Recovery Current			12		A
E_{rec}	Reverse Recovery Energy			0.35		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=15\text{A},$ $-di/dt=550\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		1.9		μC
I_{RM}	Peak Reverse Recovery Current			11		A
E_{rec}	Reverse Recovery Energy			0.65		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=15\text{A},$ $-di/dt=550\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		2.3		μC
I_{RM}	Peak Reverse Recovery Current			11		A
E_{rec}	Reverse Recovery Energy			0.76		mJ

Diode-rectifier Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=15\text{A}, T_j=150^{\circ}\text{C}$		0.96		V
I_R	Reverse Current	$T_j=150^{\circ}\text{C}, V_R=1600\text{V}$			1.0	mA

IGBT-brake Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.70	2.15	V
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		1.95		
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.25\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.2	6.0	6.8	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		1.04		nF
C_{res}	Reverse Transfer Capacitance			0.03		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.08		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=47\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		48		ns
t_r	Rise Time			47		ns
$t_{d(off)}$	Turn-Off Delay Time			185		ns
t_f	Fall Time			170		ns
E_{on}	Turn-On Switching Loss			0.96		mJ
E_{off}	Turn-Off Switching Loss			0.57		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=47\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		48		ns
t_r	Rise Time			65		ns
$t_{d(off)}$	Turn-Off Delay Time			252		ns
t_f	Fall Time			221		ns
E_{on}	Turn-On Switching Loss			1.44		mJ
E_{off}	Turn-Off Switching Loss			0.82		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=47\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		48		ns
t_r	Rise Time			67		ns
$t_{d(off)}$	Turn-Off Delay Time			283		ns
t_f	Fall Time			232		ns
E_{on}	Turn-On Switching Loss			1.66		mJ
E_{off}	Turn-Off Switching Loss			0.90		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=800\text{V}, V_{CEM} \leq 1200\text{V}$		40		A

Diode-brake Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.85	2.30	V
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		2.05		
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		2.10		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		0.5		μC
I_{RM}	Peak Reverse Recovery Current			13		A
E_{rec}	Reverse Recovery Energy			0.28		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		0.7		μC
I_{RM}	Peak Reverse Recovery Current			14		A
E_{rec}	Reverse Recovery Energy			0.48		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		0.8		μC
I_{RM}	Peak Reverse Recovery Current			15		A
E_{rec}	Reverse Recovery Energy			0.58		mJ

NTC Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			22.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=1486.1\Omega$	-5		5	%
P_{25}	Power Dissipation				200	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		4000		K

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT-inverter)		1.147	1.262	K/W
	Junction-to-Case (per Diode-inverter)		1.931	2.124	
	Junction-to-Case (per Diode-rectifier)		1.253	1.378	
	Junction-to-Case (per IGBT-brake)		1.468	1.615	
	Junction-to-Case (per Diode-brake)		2.182	2.400	
R_{thCH}	Case-to-Heatsink (per IGBT-inverter)		0.589		K/W
	Case-to-Heatsink (per Diode-inverter)		0.992		
	Case-to-Heatsink (per Diode-rectifier)		0.643		
	Case-to-Heatsink (per IGBT-brake)		0.754		
	Case-to-Heatsink (per Diode-brake)		1.121		
	Case-to-Sink (per Module)		0.036		
M	Mounting Torque, Screw M4	2.0		2.2	N.m
G	Weight of Module		26		g

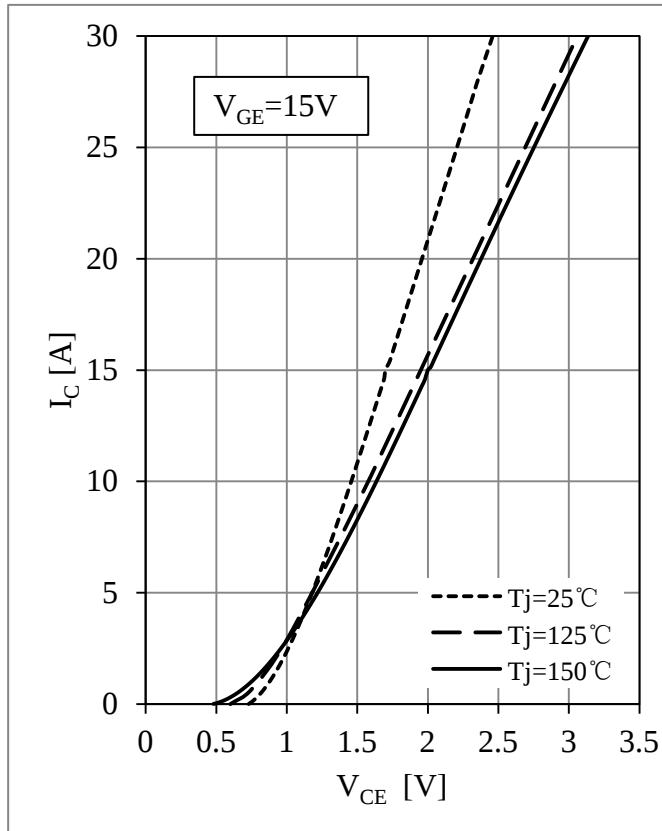


Fig 1. IGBT-inverter Output Characteristics

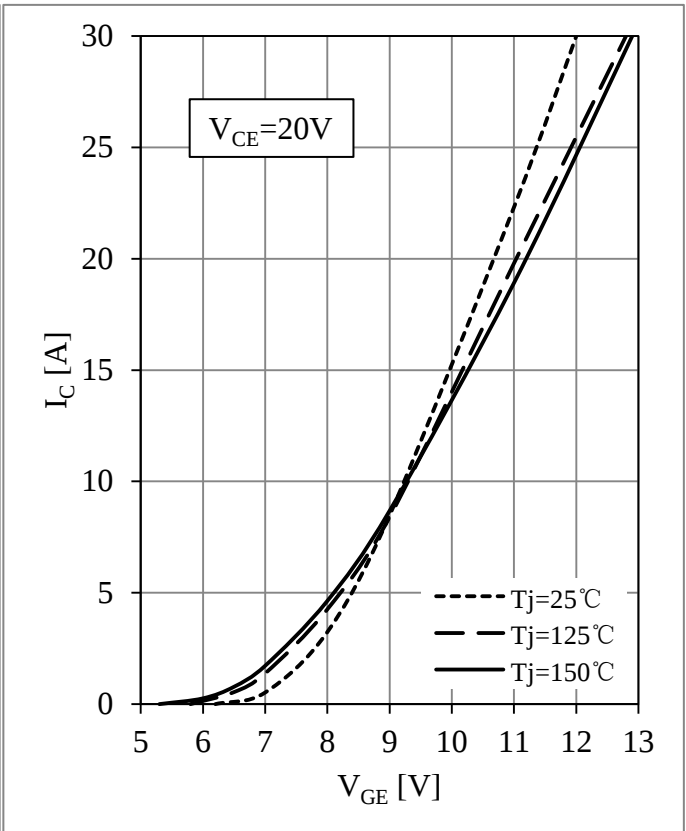
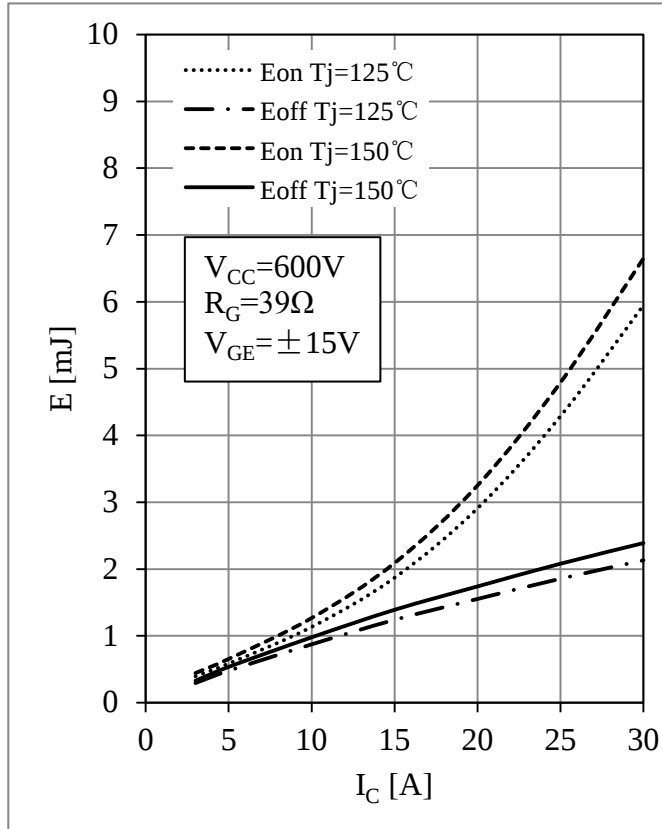
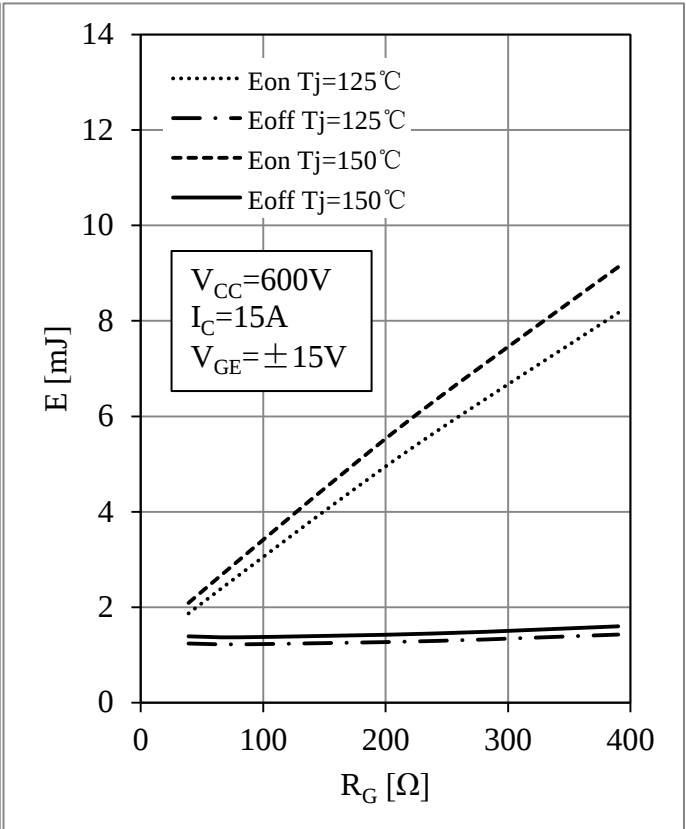


Fig 2. IGBT-inverter Transfer Characteristics

Fig 3. IGBT-inverter Switching Loss vs. I_C Fig 4. IGBT-inverter Switching Loss vs. R_G

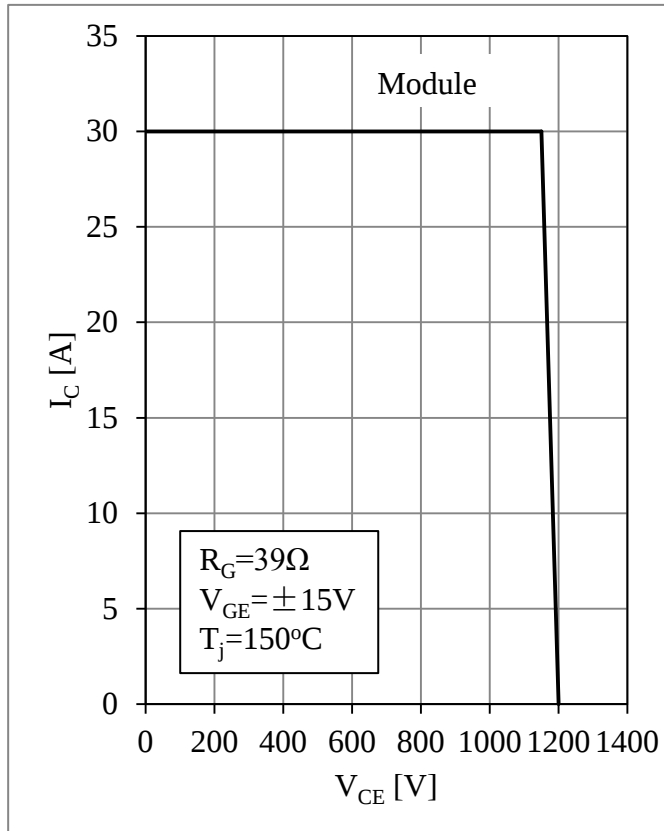


Fig 5. IGBT-inverter RBSOA

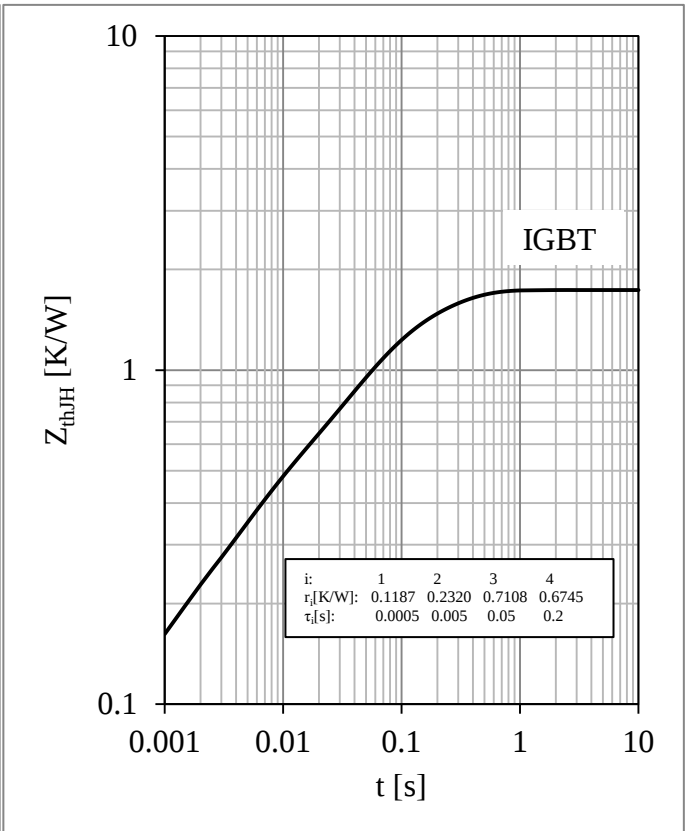


Fig 6. IGBT-inverter Transient Thermal Impedance

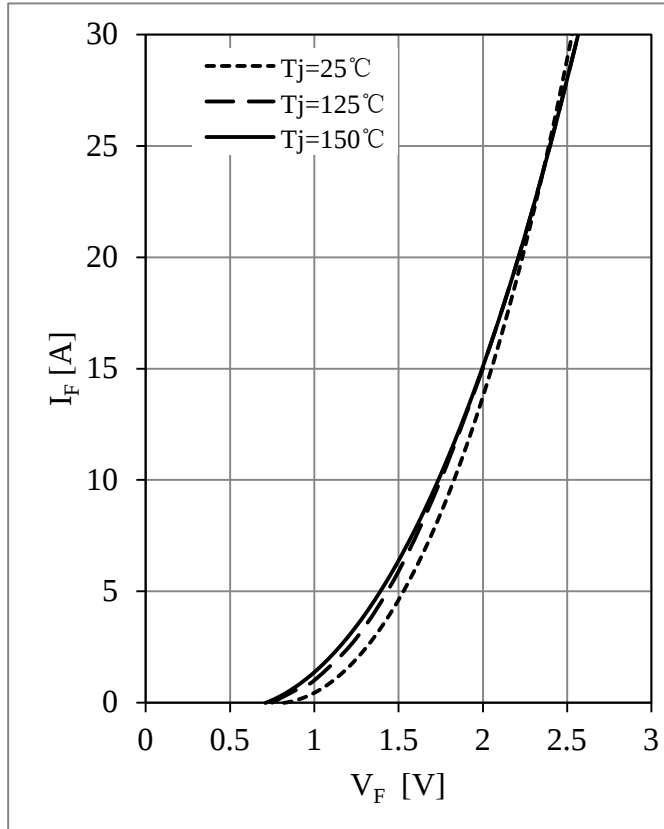
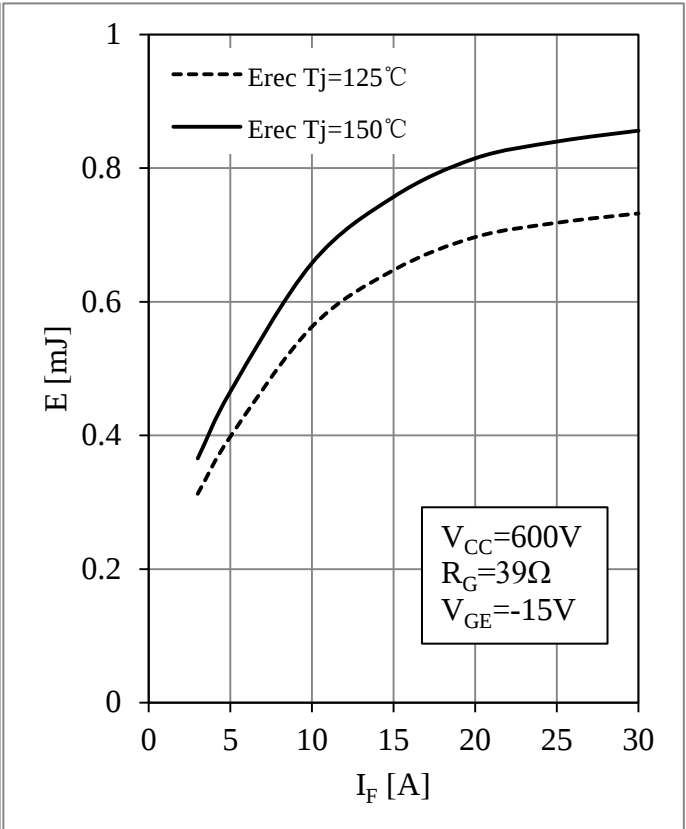
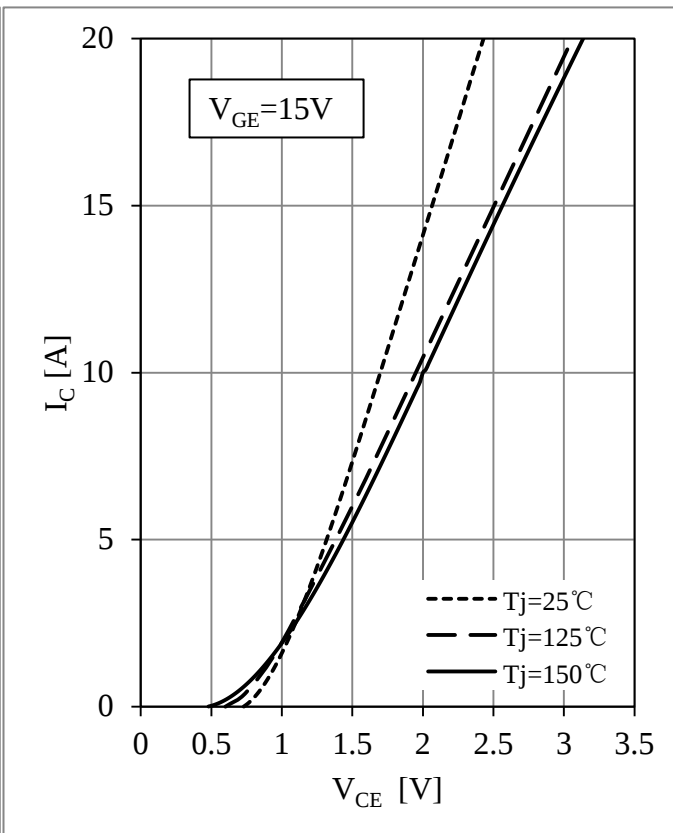
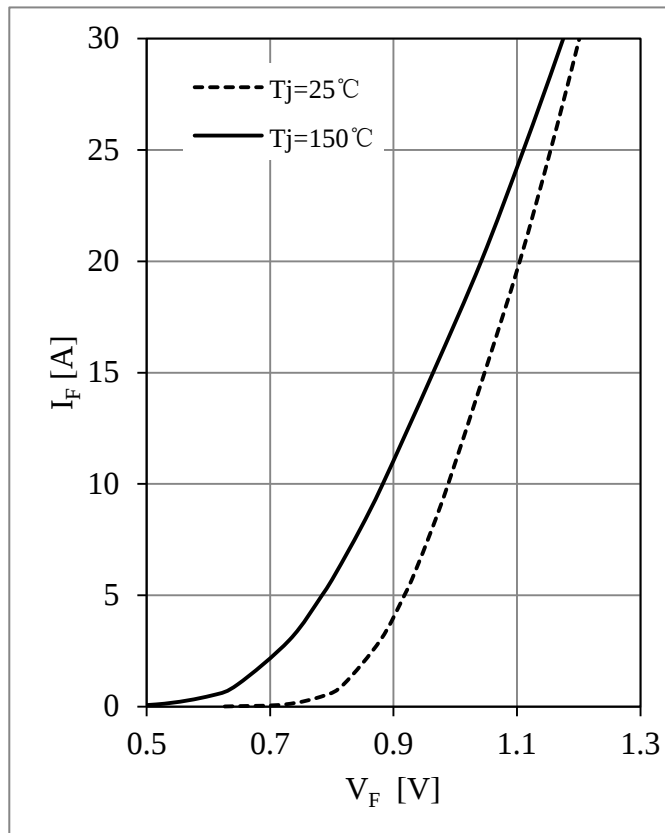
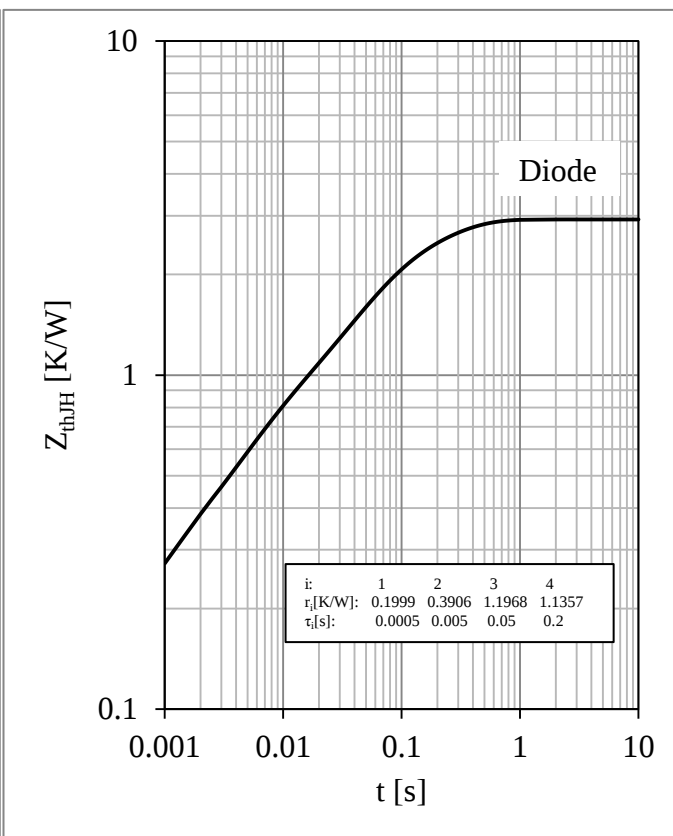
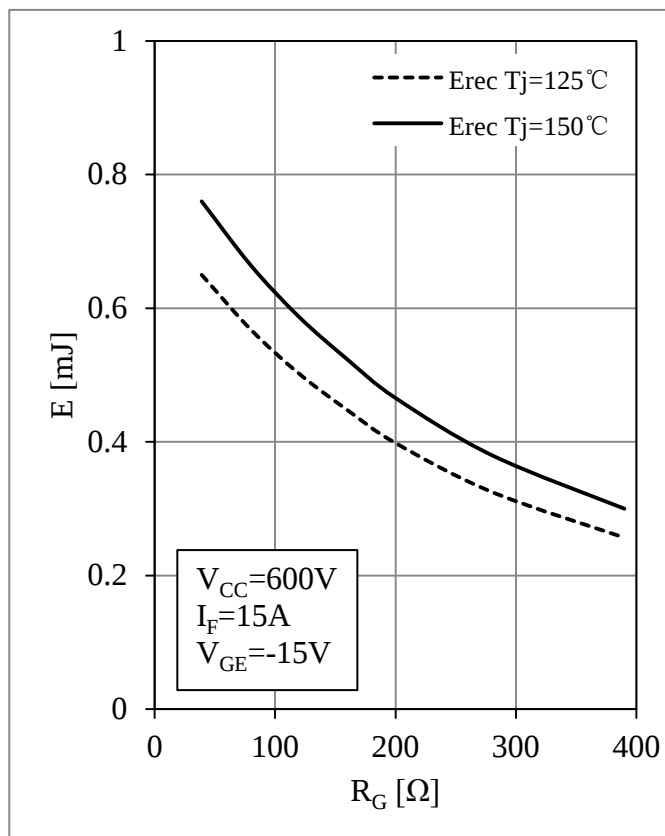


Fig 7. Diode-inverter Forward Characteristics

Fig 8. Diode-inverter Switching Loss vs. I_F



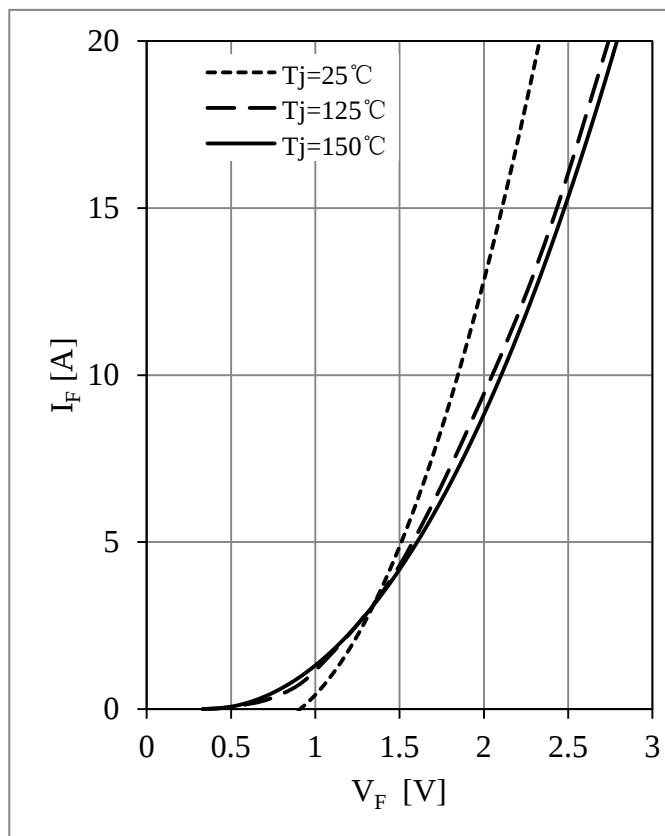


Fig 13. Diode-brake Forward Characteristics

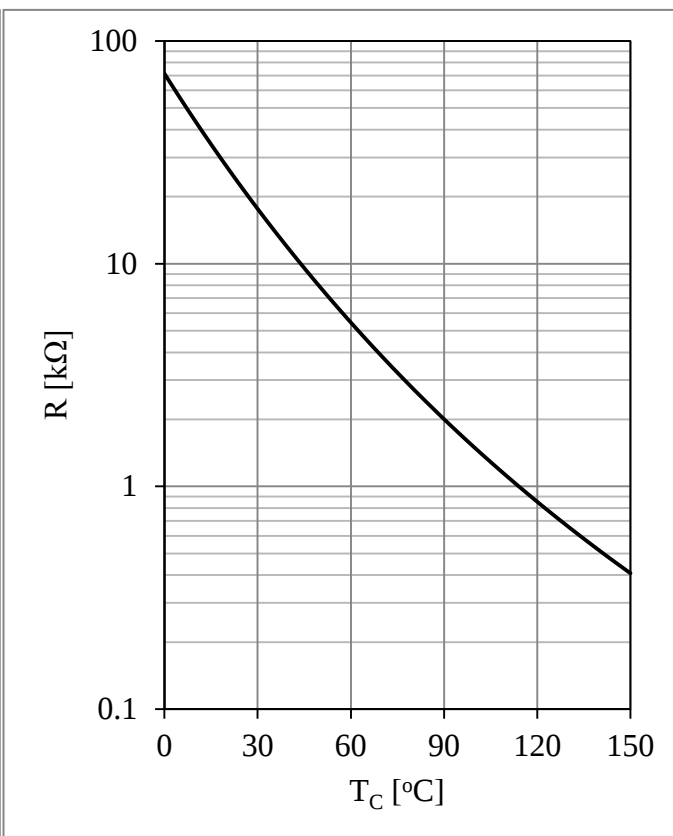
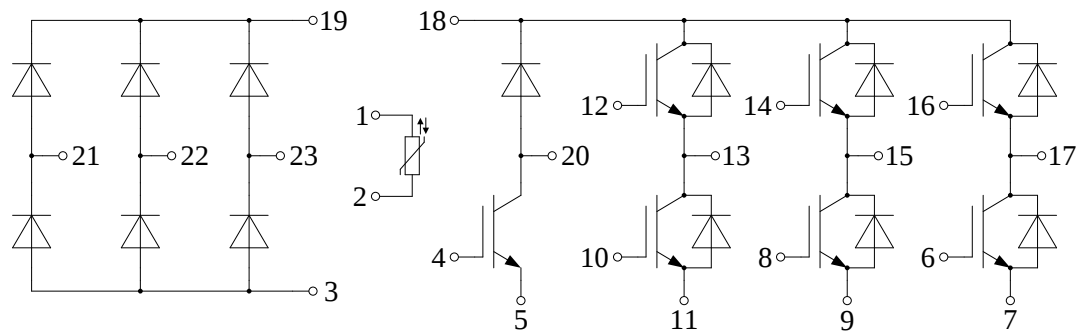


Fig 14. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters

